

Academician Ninoslav Stojadinović

Bibliography

CHAPTERS IN INTERNATIONAL BOOKS

1. Z. Stamenković and N. **Stojadinović**, "Computer-Aided Analysis and Forecast of Integrated Circuit Yield", in "*The Computer Engineering Handbook*", edited by V. Oklobžija, CRC Press, Boca Raton, pp. 47.1-47.24 (2001) ISBN-10: 0849308852 ISBN-13: 978-0849308857
2. Z. Stamenković and N. **Stojadinović**, "Computer-Aided Analysis and Forecast of Integrated Circuit Yield", in "*Digital Design and Fabrication*", edited by V. Oklobžija, CRC Press, Boca Raton, pp. 24.1-24.24 (2007) Print ISBN: 978-0-8493-8602-2, eBook ISBN: 978-0-8493-8604-6
3. D. Danković, I. Manić, S. Djorić-Veljković, V. Davidović, S. Golubović, and N. **Stojadinović**, "Implications of Negative Bias Temperature Instability in Power MOS Transistors" in *Micro Electronic and Mechanical Systems*, edited by Kenichi Takahata, IN-TECH Press, Boca Raton, pp. 19.319-19.342 (2009) ISBN: 978-953-307-027-8
4. N. **Stojadinović**, I. Manić, D. Danković, S. Djorić-Veljković, V. Davidović, A. Prijić, S. Golubović, and, Z. Prijić, "*Negative Bias Temperature Instability in Thick Gate Oxides for Power MOS Transistors*" in *Bias Temperature Instability for Devices and Circuits*, edited by Tibor Grasser, Springer Science+Business Media New York, pp. 533-559 (2014) ISBN: 978-1-4614-7908-6 (Print) 978-1-4614-7909-3 DOI 10.1007/978-1-4614-7909-3

PAPERS IN INTERNATIONAL JOURNALS

1. N. **Stojadinović**, "A New Analytical Expression for the Impurity Profile of Hyperabrupt Varicap Diodes", *Physica Status Solidi (a)*, vol. 43, pp. K91-94 (1977) ISSN: 0031-8965, DOI: 10.1002/pssa.2210430164
2. N.D. **Stojadinović** and S.D. Ristić, "Effects of Emitter Diffusion-Induced Stresses on Common-Emitter Current Gain of Silicon Planar Transistors", *Physica Status Solidi (a)*, vol. 51, pp. K83-88 (1979) ISSN: 0031-8965, DOI: 10.1002/pssa.2210510155
3. R.S. Popović and N.D. **Stojadinović**, "Dependence of Dislocations on Emitter Phosphorus Diffusion Conditions and Their Effects on Electrical Characteristics of Silicon Planar NPN Transistors", *Physica Status Solidi (a)*, vol. 52, pp. 433-440 (1979) ISSN: 0031-8965, DOI: 10.1002/pssa.2210520210
4. N.D. **Stojadinović**, "Effects of Emitter Edge Dislocations on the Low-Frequency Noise of Silicon Planar n-p-n Transistors", *Electronics Letters*, vol. 15, pp. 340-343 (1979) ISSN: 0013-5194, DOI: 10.1049/el:20020281
5. N.D. **Stojadinović**, "Conditions for the Creation of Dislocations by Diffusion of Phosphorus into Silicon", *Physica Status Solidi (a)*, vol. 54, pp. K5-10 (1979) ISSN: 0031-8965, DOI: 10.1002/pssa.2210540156
6. N.D. **Stojadinović** and R.S. Popović, "A New Method for Elimination of Emitter Edge Dislocations of Silicon Planar NPN Transistors", *Physica Status Solidi (a)*, vol. 55, pp. 307-313 (1979) ISSN: 0031-8965, DOI: 10.1002/pssa.2210550135
7. N.D. **Stojadinović**, "Emitter Diffusion-Induced Stress Effect on Common-Emitter Current Gain of Silicon Planar Transistors", *Physica Status Solidi (a)*, vol. 55, pp. K89-93, (1979) ISSN: 0031-8965, DOI: 10.1002/pssa.2210550161

8. **N.D. Stojadinović** and R.S. Popović, "Elimination of Emitter Edge Dislocations in Silicon Planar n-p-n Transistors", *Electronics Letters*, vol. 16, pp. 842-843 (1980) ISSN: 0013-5194, DOI: 10.1049/el:20020281
9. **N.D. Stojadinović**, Lj.Dj. Ristić and B.V. Vidanović, "New Technique for Fabrication of Low-Voltage Si Zener Diodes", *Electronics Letters*, vol. 17, pp. 130-132 (1981) ISSN: 0013-5194, DOI: 10.1049/el:20020281
10. **N.D. Stojadinović**, "Influence of Emitter Edge Dislocations on Reliability of Planar NPN Transistors", *Microelectronics and Reliability*, vol. 22, pp. 1113-1120 (1982) ISSN 0026-2714, DOI: 10.1016/S0026-2714(82)80564-7
11. **N.D. Stojadinović** and S.D. Ristić, "Failure Physics of Integrated Circuits and Relationship to Reliability", *Physica Status Solidi (a)*, vol. 75, pp. 11-48 (1983) (**Review Paper**) ISSN: 0031-8965, DOI: 10.1002/pssa.2210750102
12. **N. Stojadinović**, S. Dimitrijević, S. Mijalković and Z. Živić, "Reliability of N-channel and P-channel MOSTs in CMOS Integrated Circuits", *Physica Status Solidi (a)*, vol. 76, pp 357-364 (1983) ISSN: 0031-8965, DOI: 10.1002/pssa.2210760143
13. **N. Stojadinović**, "Failure Physics of Integrated Circuits - A Review", *Microelectronics and Reliability*, vol. 23, pp. 609-707 (1983) (**Review Paper**) ISSN 0026-2714, DOI: 10.1016/0026-2714(83)91158-7 10.1016/0026-2714(83)91158-7
14. **N. Stojadinović**, "Effects of Accelerated Temperature Testing on the Low-Frequency Noise of Planar NPN Transistors", *Microelectronics and Reliability*, vol. 23, pp. 899-901 (1983) ISSN 0026-2714, DOI: 10.1016/0026-2714(83)91017-X
15. Z. Živić, A. Živić and **N. Stojadinović**, "A New CMOS IC Structure and its Characterization", *Microelectronics and Reliability*, vol. 25, no. 1, pp. 123-146 (1985) ISSN 0026-2714, DOI 0026-2714(85)90453-6
16. **N. Stojadinović**, S. Dimitrijević and S. Mijalković, "Effects of High Field Stresses on Threshold Voltage of CMOS Transistors", *Microelectronics and Reliability*, vol. 25, no. 2, pp. 275-279 (1985) ISSN 0026-2714, DOI 10.1016/0026-2714(85)90013-7
17. S. Dimitrijević and **N. Stojadinović**, "Analysis of CMOS Transistor Instabilities", *Solid-State Electronics*, vol. 30, pp. 991-1003 (1987) ISSN: 0038-1101, DOI: 10.1016/0038-1101(87)90090-6 10.1016/0038-1101(87)90090-6
18. S. Dimitrijević, D. Župac and **N. Stojadinović**, "New Analytical Expression for the Drain Current of Short-Channel MOS Transistors in the Triode Region", *Electronics Letters*, vol. 23, pp. 862-864 (1987) ISSN: 0013-5194, DOI: 10.1049/el:20020281
19. S. Dimitrijević, D. Župac and **N. Stojadinović**, "Mechanisms of Positive-Gate Bias Stress Induced Instabilities in CMOS Transistors", *Microelectronics and Reliability*, vol. 27, no. 6, pp. 1001-1016 (1987) ISSN 0026-2714, DOI 10.1016/0026-2714(87)90762-1
20. S. Dimitrijević, **N. Stojadinović** and Z. Stamenković, "Yield Model for In-Line Integrated Circuit Production Control", *Solid-State Electronics*, vol. 31, no. 5, pp. 975-979 (1988) ISSN: 0038-1101, DOI: 10.1016/0038-1101(88)90054-8
21. B. Pešić, S. Dimitrijević and **N. Stojadinović**, "Sudden Failures Associated with the Gate Oxide of CMOS Transistors", *Microelectronics and Reliability*, vol. 28, no. 4, pp. 643-648 (1988) ISSN 0026-2714, DOI 10.1016/0026-2714(88)90150-3
22. S. Mijalković and **N. Stojadinović**, "Efficient Simulation of Impurity Redistribution in VLSI Fabrication Processes", *Solid-State Electronics*, vol. 31, no. 12, pp. 1689-1693 (1988) ISSN: 0038-1101, DOI: 10.1016/0038-1101(88)90065-2
23. **N. Stojadinović** and S. Dimitrijević, "Instabilities in MOS Transistors", *Microelectronics and Reliability*, vol. 29, no. 3, pp. 371-380 (1989) (**Invited Paper**) ISSN: 0026-2714, DOI: 10.1016/0026-2714(89)90623-9 10.1016/0026-2714(89)90623-9
24. S. Dimitrijević, S. Golubović, D. Župac, M. Pejović and **N. Stojadinović**, "Analysis of Gamma-Radiation Induced Instability Mechanisms of CMOS Transistors", *Solid-State Electronics*, vol. 32, no. 5, pp. 349-353 (1989) ISSN: 0038-1101, DOI: 10.1016/0038-1101(89)90122-6

25. B. Pešić, S. Dimitrijević and **N. Stojadinović**, "Investigation of Gate Oxide Breakdown in CMOS Integrated Circuits", *Microelectronics Journal*, vol. 20, no. 6, pp. 19-26 (1989) ISSN: 0026-2692, DOI: 10.1016/0026-2692(89)90064-5
26. D. Pantić, S. Mijalković and **N. Stojadinović**, "A New Multilayer Ion Implantation Model for Process Simulation", *Microelectronics Journal*, vol. 20, no. 6, pp. 5-10 (1989) ISSN: 0026-2692, DOI: 10.1016/0026-2692(89)90062-1
27. Z. Prijić, S. Dimitrijević and **N. Stojadinović**, "Analysis of Temperature Dependence of CMOS Transistors Threshold Voltage", *Microelectronics and Reliability*, vol. 31, pp. 33-37 (1991) ISSN: 0026-2714, DOI: 10.1016/0026-2714(91)90342-5
28. S. Mijalković, D. Pantić, Z. Prijić, S. Mitrović and **N. Stojadinović**, "MUSIC - A Multigrid Simulator for IC Fabrication Processes", *COMPEL: The International Journal for Computation and Mathematics in Electrical and Electronic Engineering*, vol. 10, pp. 599-610 (1991) ISSN: 0026-2714, DOI: 10.1108/eb051734
29. L. Lukasiak, B. Majkusiak, A. Jakubowski, S. Dimitrijević and **N. Stojadinović**, "A Review of Long-Channel MOS Transistor Models", *Microelectronics Journal*, vol. 22, no. 2, pp. 55-88 (1991) (**Review Paper**) ISSN: 0026-2692, DOI: 10.1016/0026-2692(91)90025-1
30. D. Petković and **N. Stojadinović**, "Polycrystalline Silicon Thin Film Resistors with Irreversible Resistance Transition", *Microelectronics Journal*, vol. 23, no. 1, pp. 51-58 (1992) ISSN: 0026-2692, DOI: 10.1016/0026-2692(92)90096-J
31. S. Golubović, M. Pejović, S. Dimitrijević and **N. Stojadinović**, "UV-Radiation Annealing of the Electron- and X-Irradiation Damaged CMOS Transistors", *Physica Status Solidi (a)*, vol. 129, pp. 569-575 (1992)) ISSN: 0031-8965, DOI: 10.1002/pssa.2211290227
32. Z. Stamenković and **N. Stojadinović**, "New Defect Size Distribution Function for Estimation of Chip Critical Area in Integrated Circuit Yield Models", *Electronics Letters*, vol. 28, pp. 528-530 (1992) ISSN: 0013-5194, DOI: 10.1049/el:20020281
33. Z. Stamenković and **N. Stojadinović**, "Chip Yield Modelling Related to Photolithographic Defects", *Microelectronics and Reliability*, vol. 32, pp. 663-668 (1992) ISSN: 0026-2714, DOI: 10.1016/0026-2714(92)90623-S
34. Z.D. Prijić, S.S. Dimitrijević and **N. Stojadinović**, "The Determination of Zero-Temperature-Coefficient Point in CMOS Transistors", *Microelectronics and Reliability*, vol. 32, pp. 769-773 (1992) ISSN 0026-2714, DOI: 10.1016/0026-2714(92)90041-I
35. D. Pantić, S. Mijalković and **N. Stojadinović**, "The Efficient Simulation of Point Defects Diffusion by an Adaptive Multigrid Method", *Microelectronic Engineering*, vol. 19, pp. 789-794 (1992) ISSN: 0167-9317, DOI: 10.1016/0167-9317(92)90546-4
36. Z. Pavlović, Z. Prijić, S. Ristić and **N. Stojadinović**, "Temperature Dependence of ON-Resistance in Low-Voltage Power VDMOS Transistors", *Microelectronics Journal*, vol. 24, pp. 115-124 (1993) ISSN 0026-2692, DOI: 10.1016/0026-2692(93)90106-O
37. T. Brozek, B. Pešić, A. Jakubowski and **N. Stojadinović**, "Breakdown Properties of Thin Oxides in Irradiated MOS Capacitors", *Microelectronics and Reliability*, vol. 33, pp. 649-657 (1993) ISSN: 0026-2714, DOI: 10.1016/0026-2714(93)90271-Y
38. Z. Prijić, Z. Pavlović, S. Ristić and **N. Stojadinović**, "Zero-Temperature Coefficient (ZTC) Biasing of Power VDMOS Transistor", *Electronics Letters*, vol. 29, pp. 435-437 (1993) ISSN: 0013-5194, DOI: 10.1049/el:20020281
39. Z. Stamenković, S. Dimitrijević and **N. Stojadinović**, "Integrated Circuit Production Yield Assurance Based on Yield Analysis", *Microelectronics Journal*, vol. 24, no. 7, pp. 819-822 (1993) ISSN: 0026-2692, DOI: 10.1016/0026-2692(93)90026-B
40. D. Petković and **N. Stojadinović**, "Reliability of Polysilicon Thin Film Resistors with Irreversible Resistance Transition", *Microelectronics and Reliability*, vol. 33, pp. 785-791 (1993) ISSN: 0026-2714, DOI: 10.1016/0026-2714(93)90250-3

41. **N. Stojadinović**, "Quarter Century of Field of Microelectronics and 'Microelectronics Journal': Joint Crossroads for Further Progress and Development", *Microelectronics Journal*, vol. 25, no. 1, pp. iii-ix (1994) (**Review Paper**) ISSN:0026-2692, DOI:10.1016/0026-2692(94)90148-1
42. D. Pantić, S. Mijalković and **N. Stojadinović**, "An Efficient Multiparticle Diffusion Simulation by an Adaptive Multigrid Method", *Microelectronics Journal*, vol. 25, no. 2, pp. 79-97 (1994) ISSN: 0026-2692 DOI: 10.1016/0026-2692(94)90106-6
43. **N. Stojadinović**, S. Djorić, S. Golubović and V. Davidović, "Separation of Irradiation Induced Gate Oxide Charge and Interface Traps Effects in Power VDMOSFETs", *Electronics Letters*, vol. 30, no. 23, pp. 1992-1993 (1994) ISSN: 0013-5194, DOI: 10.1049/el:20020281
44. S. Mitrović, S. Mijalković and **N. Stojadinović**, "Locally one-Dimensional Approach to Diffusion Process Simulation in Nonplanar Domains", *Electronics Letters*, vol. 31, pp. 1788-1789 (1995) ISSN: 0013-5194, DOI: 10.1049/el:20020281
45. **N. Stojadinović**, S. Golubović, S. Djorić and S. Dimitrijević, "Analysis of Gamma-Irradiation Induced Degradation Mechanisms in Power VDMOSFETs", *Microelectronics and Reliability*, vol. 35, no. 3, pp. 587-602 (1995) ISSN: 0026-2714, DOI:10.1016/0026-2714(95)93077-N
46. **N. Stojadinović**, M. Pejović, S. Golubović, G. Ristić, V. Davidović and S. Dimitrijević, "Effect of Radiation-Induced Oxide-Trapped Charge on Mobility in p-Channel MOSFETs", *Electronics Letters*, vol. 31, pp. 497-498 (1995) ISSN: 0013-5194, DOI: 10.1049/el:20020281
47. Z. Savić, B. Radjenović, M. Pejović and **N. Stojadinović**, "The Contribution of Border Traps to the Threshold Voltage Shift in pMOS Dosimetric Transistors", *IEEE Trans. on Nuclear Science*, vol. 42, pp. 1445-1454 (1995) ISSN: 0018-9499, DOI: 10.1109/23.467722
48. S. Dimitrijević, D. Župac and **N. Stojadinović**, comments on "Substrate-Bias-Dependent Threshold-Voltage Model of Short-Channel MOSFET", *Solid-State Electronics*, vol. 38, no. 1, pp. 267 (1995) ISSN: 0038-1101, DOI: 10.1016/0038-1101(94)00151-5
49. Z. Stamenković, **N. Stojadinović** and S. Dimitrijević, "Modeling of Integrated Circuit Yield Loss Mechanisms", *IEEE Trans. on Semiconductor Manufacturing*, vol. 9, no. 22, pp. 270-272 (1996) ISSN: 0894-6507, DOI: 10.1109/66.492821
50. P. Habaš, Z. Prijić, D. Pantić and **N. Stojadinović**, "Charge-Pumping Characterization of SiO₂/Si Interface in Virgin and Irradiated Power VDMOSFETs", *IEEE Transactions on Electron Devices*, vol. 43, no. 12, pp. 2197-2209 (1996) ISSN: 0018-9383, DOI: 10.1109/16.544392
51. Z. Prijić, P. Igić, Z. Pavlović and **N. Stojadinović**, "Simple Method for the Extraction of Power VDMOS Transistor Parameters", *Microelectronics Journal*, vol. 27, no. 6, pp. 567-570 (1996) ISSN: 0026-2692, DOI: 10.1016/0026-2692(95)00120-4
52. N. Tošić, B. Pešić and **N. Stojadinović**, "High-Temperature-Reverse-Bias Testing of Power VDMOS Transistors", *Microelectronics and Reliability*, vol. 37, no. 10-11, pp. 1759-1762 (1997), ISSN: 0026-2714, DOI: 10.1016/S0026-2714(97)00155-8
53. D. Pantić, T. Trajković and **N. Stojadinović**, "A new Technology Computer Aided Design (TCAD) System Based on Neural Network Models", *Microelectronics Journal*, vol. 29, no. 1-2, pp. 1-4 (1998) ISSN 0026-2692, DOI: 10.1016/S0026-2692(97)00016-5
54. T. Trajković, P. Igić and **N. Stojadinović**, "A. Novel Method for Extraction of MOS Transistor Model Parameters Using Neural Networks", *Microelectronics Reliability*, vol. 38, no. 3 pp. 331-335 (1998) ISSN: 0026-2714, DOI: 10.1016/S0026-2714(97)00177-7
55. **N. Stojadinović**, S. Golubović, V. Davidović, S. Djorić-Veljković and S. Dimitrijević, "Modeling Radiation-Induced Mobility Degradation in MOSFETs", *Phys. Stat. Sol. (a)*, vol. 169, no. 1, pp. 63-66 (1998) ISSN: 0031-8965, DOI: 10.1002/(SICI)1521-396X(199809)169:1<63::AID-PSSA63>3.3.CO;2-W
56. Z. Pavlović, I. Manić, Z. Prijić and **N. Stojadinović**, "Temperature Distribution in the Cells of Low-Voltage Power VDMOS transistor", *Microelectronics Journal*, vol. 30, no. 2, pp. 109-113 (1999) ISSN 0026-2692, DOI: 10.1016/S0026-2692(98)00096-2

57. S. Golubović, S. Djorić-Veljković, V. Davidović, and **N. Stojadinović**, "Modeling of γ -Irradiation and Lowered Temperature Effects in Power VDMOS Transistors", *Japanese J. Appl. Phys.*, vol. 38, no. 8, pp. 4699-4702 (1999) DOI: 10.1143/JJAP.38.4699
N. Stojadinović, S. Golubović, S. Djorić-Veljković, and V. Davidović, "Correction to "Modeling of γ -irradiation and lowered temperature effects in power VDMOS transistors"", *Japanese J. Appl. Phys.*, vol. 40 (3A), p. 1530 (2001) ISSN: 0021-4922, DOI: 10.1143/JJAP.38.4699
58. I. Manić, Z. Pavlović, Z. Prijić, V. Davidović and **N. Stojadinović**, "Analytical Modelling of Electrical Characteristics in γ -Irradiated Power VDMOS Transistors", *Microelectronics Journal*, vol. 32, no. 5-6, pp. 485-490 (2001) ISSN: 0026-2692, DOI: 10.1016/S0026-2692(01)00019-2
59. **N. Stojadinović**, I. Manić, S. Djorić-Veljković, V. Davidović, S. Golubović, and S. Dimitrijević, "Mechanisms of Positive Gate Bias Stress Induced Instabilities in Power VDMOSFETs", *Microelectronics Reliability*, vol. 41, no. 9-10, pp. 1373-1378 (2001) ISSN: 0026-2714, DOI: 10.1016/S0026-2714(01)00143-3
60. **N. Stojadinović**, S. Djorić-Veljković, I. Manić, V. Davidović and S. Golubović, "Radiation Hardening of Power VDMOSFETs Using Electrical Stress", *Electronics Letters*, vol. 38, no. 9, pp. 431-432 (2002) ISSN: 0013-5194, DOI: 10.1049/el:20020281
61. **N. Stojadinović**, I. Manić, S. Djorić-Veljković, V. Davidović, S. Golubović and S. Dimitrijević, "Effects of High Electric Field and Elevated-Temperature Bias Stressing on Radiation Response in Power VDMOSFETs", *Microelectronics Reliability*, vol. 42, no. 4-5, pp. 669-677 (2002) ISSN: 0026-2714, DOI: 10.1016/S0026-2714(02)00039-2
62. **N. Stojadinović**, S. Djorić-Veljković, I. Manić, V. Davidović, and S. Golubović, "Effects of Burn-in Stressing on Radiation Response of Power VDMOSFETs", *Microelectronics Journal*, vol. 33, no. 11, pp. 899-905 (2002) ISSN: 0026-2692, DOI: 10.1016/S0026-2692(02)00121-0
63. **N. Stojadinović**, I. Manić, S. Djorić-Veljković, V. Davidović, D. Danković, S. Golubović and S. Dimitrijević, "Mechanisms of Spontaneous Recovery in Positive Gate Bias Stressed Power VDMOSFETs", *Microelectronics Reliability*, vol. 42, no. 9-11, pp. 1465-1468 (2002) ISSN: 0026-2714, DOI: 10.1016/S0026-2714(02)00171-3
64. S. Djorić-Veljković, I. Manić, V. Davidović, S. Golubović, and **N. Stojadinović**, "Effects of Burn-in Stressing on Post-Irradiation Annealing Response of Power VDMOSFETs", *Microelectronics Reliability*, vol. 43, no. 9-11, pp. 1455-1460 (2003) ISSN: 0026-2714, DOI: 10.1016/S0026-2714(03)00258-0
65. B. Pešić, Lj. Vračar, **N. Stojadinović**, M. Pecovska-Djordjević, and N. Novkovski, "Stress-Induced Leakage Currents in Thin Silicon Dioxide Films", *Journal of Materials Science, Materials in Electronics*, vol. 14, no. 10-12, pp. 805-807 (2003) ISSN: 0957-4522, DOI: 10.1023/A:1026169624327
66. D.N. Kouvatso, V. Davidović, G.J. Papaioannou, **N. Stojadinović**, L. Michalas, M. Exarchos, A.T. Voutsas, and D. Goustouridis, "Effects of Hot Carrier and Irradiation Stresses on Advanced Excimer Laser Annealed Polycrystalline Silicon Thin Film Transistors", *Microelectronics Reliability*, vol. 44, no. 9-11, pp. 1631-1636 (2004) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2004.07.082
67. **N. Stojadinović**, I. Manić, V. Davidović, D. Danković, S. Djorić-Veljković, S. Golubović, and S. Dimitrijević, "Effects of Electrical Stressing in Power VDMOSFETs", *Microelectronics Reliability*, vol. 45, no. 1, pp. 115-122 (2005) (**Invited Paper**) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2004.09.002
68. **N. Stojadinović**, D. Danković, S. Djorić-Veljković, V. Davidović, I. Manić, and S. Golubović, "Negative Bias Temperature Instability Mechanisms in p-Channel Power VDMOSFETs", *Microelectronics Reliability*, vol. 45, no. 9-11, pp. 1343-1348 (2005) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2005.07.018

69. **N. Stojadinović**, I. Manić, V. Davidović, D. Danković, S. Djorić-Veljković, S. Golubović, and S. Dimitrijević, "Electrical Stressing Effects in Commercial Power VDMOSFETs", *IEE Proc. - Circuits, Devices and Systems*, vol. 153, no. 3, pp. 281-288 (2006) ISSN: 1350-2409, DOI: 10.1049/ip-eds:20050050
70. D. Danković, I. Manić, S. Djorić-Veljković, V. Davidović, S. Golubović, and **N. Stojadinović** "NBT Stress-Induced Degradation and Lifetime Estimation in p-channel Power VDMOSFETs", *Microelectronics Reliability*, vol. 46, no. 9-11, pp. 1828-1833 (2006) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2006.07.077
71. D. Danković, I. Manić, V. Davidović, S. Djorić-Veljković, S. Golubović, **N. Stojadinović**, "Negative Bias Temperature Instabilities in Sequentially Stressed and Annealed in p-Channel Power VDMOSFETs", *Microelectronics Reliability*, vol. 47, no. 9-11, pp. 1400-1405 (2007) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2007.07.022
72. V. Davidović, DN. Kouvatsov, **N. Stojadinović** and A.T. Voutsas, "Influence of Polysilicon Film Thickness on Radiation Response of Advanced Excimer Laser Annealed Polycrystalline Thin Film Transistors", *Microelectronics Reliability*, vol. 47, no. 9-11, pp. 1841 - 1845 (2007) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2007.07.025
73. I. Manić, S. Djorić-Veljković, V. Davidović, D. Danković, S. Golubović, **N. Stojadinović**, "Mechanisms of Spontaneous Recovery in DC Gate Bias Stressed Power VDMOSFETs", *IET Circuits, Devices and Systems*, vol. 2, no. 2, pp. 213-221 (2008) ISSN: 1751-858X, DOI: 10.1049/iet-cds:20070173 10.1049/iet-cds:20070173
74. E. Atanassova, **N. Stojadinović**, A. Paskaleva, D. Spasov, Lj. Vračar, M. Georgieva, "Constant Voltage Stress Induced Current in Ta₂O₅ Stacks and Dependence on a Gate Electrode", *Semiconductor Science and Technology*, vol. 23, Art. no. 075017 p. 9 (2008) ISSN: 0268-1242 (Print) 1361-6641 DOI: 10.1088/0268-1242/23/7/075017
75. V. Davidović, **N. Stojadinović**, D. Danković, S. Golubović, I. Manić, S. Djorić-Veljković, and S. Dimitrijević, "Turn-Around of Threshold Voltage in Gate Bias Stressed p-Channel Power Vertical Double-Diffused Metal-Oxide-Semiconductor Transistors", *Japanese J. Appl. Phys.*, vol. 47, pp. 6272-6276 (2008) ISSN: 1347-4065 (online) 0021-4922 (print) DOI: 10.1143/JJAP.47.6272 10.1143/JJAP.47.6272
76. E. Atanassova, **N. Stojadinović**, and A. Paskaleva, "Degradation Behaviour of T₂O₅ Stacks and its Dependence on the Gate Electrode", *Microelectronics Reliability*, vol. 48, no. 8-9, pp. 1193 - 1197 (2008) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2008.07.006
77. D. Danković, I. Manić, V. Davidović, S. Djorić-Veljković, S. Golubović, and **N. Stojadinović**, "Negative Bias Temperature Instability in n-Channel Power VDMOSFETs", *Microelectronics Reliability*, vol. 48, no. 8-9, pp. 1313 - 1317 (2008) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2008.06.015
78. I. Manić, D. Danković, S. Djorić-Veljković, V. Davidović, S. Golubović, and **N. Stojadinović**, "Effects of Low Gate Bias Annealing in NBT Stressed p-Channel Power VDMOSFETs", *Microelectronics Reliability*, vol. 49, no. 9-11, pp. 1003 - 1007 (2009) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2009.07.010
79. **N. Stojadinović**, D. Danković, I. Manić, A. Prijić, V. Davidović, S. Djorić-Veljković, S. Golubović, and Z. Prijić, "Threshold Voltage Instabilities in p-Channel Power VDMOSFETs Under Pulsed NBT Stress", *Microelectronics Reliability*, vol. 50, no. 9-11, pp. 1278 - 1282 (2010) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2010.07.122
80. I. Manić, E. Atanassova, **N. Stojadinović**, D. Spasov, A. Paskaleva, "Hf-doped Ta₂O₅ Stacks Under Constant Voltage Stress", *Microelectronic Engineering*, vol. 88, no. 3, pp. 305 - 313 (2011) ISSN: 0167-9317, DOI: 10.1016/j.mee.2010.11.033
81. S. Djorić-Veljković, I. Manić, V. Davidović, D. Danković, S. Golubović, and **N. Stojadinović**, "Annealing of Radiation-Induced Defects in Burn-In Stressed Power VDMOSFETs", *Nuclear Technology & Radiation Protection*, vol. 26, no. 1, pp. 18 - 24 (2011) ISSN: 1451-3994, DOI: 10.2298/NTRP1101018D
82. I. Manić, D. Danković, A. Prijić, V. Davidović, S. Djorić-Veljković, S. Golubović, Z. Prijić, and **N. Stojadinović**, "NBTI Related Degradation and Lifetime Estimation in p-Channel Power

- VDMOSFETs Under the Static and Pulsed NBT Stress Conditions", *Microelectronics Reliability*, vol. 51, no. 9-11, pp. 1540 - 1543 (2011) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2011.06.004
83. A. Prijić, D. Danković, Lj. Vračar, I. Manić, Z. Prijić, and **N. Stojadinović**, "A Method for Negative Bias Temperature Instability (NBTI) Measurements on Power VDMOS Transistors", *Measurement Science & Technology*, vol. 23, no. 8, Art. No. 085003 (2012) ISSN: 0957-0233, DOI: 10.1088/0957-0233/23/8/085003
 84. D. Danković, I. Manić, A. Prijić, V. Davidović, S. Djorić-Veljković, S. Golubović, Z. Prijić, and **N. Stojadinović**, "Effects of Static and Pulsed Negative Bias Temperature Stressing on Lifetime in p-Channel Power VDMOSFETs", *Informacije MIDEM-Journal of Microelectronics Electric Components and Materials*, vol. 43, iss. 1, pp. 58-66 (2013) ISSN: 0352-9045 Accession Number: WOS:000318180100008
 85. E. Atanassova, **N. Stojadinović**, D. Spasov, I. Manić, A. Paskaleva, "Time-Dependent Dielectric Breakdown in Pure and Lightly Al-Doped Ta₂O₅ Stacks", *Semiconductor Science and Technology*, vol. 28, no. 5, art. no. 055006 (2013) ISSN: 0268-1242, DOI: 10.1088/0268-1242/28/5/055006
 86. S. Djorić-Veljković, I. Manić, V. Davidović, D. Danković, S. Golubović, and **N. Stojadinović**, "The Comparison of Gamma-Radiation and Electrical Stress Influences on Oxide and Interface Defects in Power VDMOSFETs", *Nuclear Technology & Radiation Protection*, vol. 28, no. 4, pp. 406-414 (2013) ISSN: 1451-3994 DOI: 10.2298/NTRP1304406D
 87. I. Manić, D. Danković, A. Prijić, Z. Prijić, **N. Stojadinović**, "Measurement of NBTI Degradation in P-Channel Power VDMOSFETs", *Informacije MIDEM, Journal of Microelectronics, Electric Components and Materials*, vol. 44, no. 4, pp. 280-287 (2014) ISSN: 0352-9045 UDK: 621.3:(53+54+621+66)
 88. S. Djorić-Veljković, I. Manić, V. Davidović, D. Danković, S. Golubović, and **N. Stojadinović**, "Annealing Influence on Recovery of Electrically Stressed Power Vertical Double-Diffused Metal Oxide Semiconductor Transistors", *Japanese Journal of Applied Physics*, vol. 54, iss. 6, art. n. 064101-1-7 (2015) ISSN: 0021-4922 DOI: 10.7567/JJAP.54.064101
 89. D. Danković, I. Manić, A. Prijić, S. Djorić-Veljković, V. Davidović, **N. Stojadinović**, Z. Prijić, S. Golubović, "Negative Bias Temperature Instability in P-Channel Power VDMOSFETs: Recoverable Versus Permanent Degradation", *Semiconductor Science and Technology*, vol. 30, p. 105009 (2015) ISSN: 0268-1242 DOI: 10.1088/0268-1242/30/10/105009
 90. D. Danković, **N. Stojadinović**, Z. Prijić, I. Manić, V. Davidović, A. Prijić, S. Djorić-Veljković, S. Golubović, "Analysis of Recoverable and Permanent Components of Threshold Voltage Shift in NBT Stressed P-Channel Power VDMOSFET", *Chinese Physics B*, vol. 24, no. 10, pp. 106601-1-9 (2015) ISSN: 1674-1056 DOI: 10.1088/1674-1056/24/10/106601
 91. V. Davidović, D. Danković, A. Ilić, I. Manić, S. Golubović, S. Djorić-Veljković, Z. Prijić, **N. Stojadinović**, "NBTI and Irradiation Effects in P-Channel Power VDMOS Transistors", *IEEE Transactions on Nuclear Science*, vol. 63, no. 2, pp. 1268-1275 (2016) ISSN: 0018-9499, DOI:10.1109/TNS.2016.2533866
 92. D. Danković, I. Manić, V. Davidović, A. Prijić, M. Marjanovic, A. Ilic, Z. Prijić, **N. Stojadinović**, "On the Recoverable and Permanent Components of NBTI in P-Channel Power VDMOSFETs", *IEEE Transactions on Device and Materials Reliability*, vol. 16, no. 4, pp. 522-531, art. no. 7536114 (2016) ISSN: 1530-4388 DOI: 10.1109/TDMR.2016.2598557
 93. V. Davidović, D. Danković, A. Ilić, I. Manić, S. Golubović, S. Djorić-Veljković, Z. Prijić, A. Prijić, and **N. Stojadinović**, "Effects of consecutive irradiation and bias temperature stress in p-channel power vertical double-diffused metal oxide semiconductor transistors", *Japanese Journal of Applied Physics*, vol. 57, pp. 044101-1-044101-10, (2018) ISSN: 0021-4922 DOI: 10.7567/JJAP.57.044101
 94. D. Danković, I. Manić, A. Prijić, V. Davidović, Z. Prijić, S. Golubović, S. Djorić-Veljković, A. Paskaleva, D. Spasov, **N. Stojadinović**, "A review of pulsed NBTI in P-channel power VDMOSFETs ", *Microelectronics Reliability*, vol. 82, pp. 28 - 36 (2018) (**Invited Paper**) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2018.01.003

95. **N. Stojadinović**, S. Djorić-Veljković, V. Davidović, S. Golubović, S. Stankovic, A. Prijić, Z. Prijić, I. Manić, D. Danković, "NBTI and irradiation related degradation mechanisms in power VDMOS transistors", *Microelectronics Reliability*, vol. 88-90, pp. 135-141 (2018) ISSN: 0026-2714, DOI: 10.1016/j.microrel.2018.07.138 (**Invited Paper**)
96. D. Danković, N. Mitrović, Z. Prijić, **N. Stojadinović**, "Modeling of NBTS Effects in P-Channel Power VDMOSFETs", *IEEE Transactions on Device and Materials Reliability*, vol. 20, no. 1, pp. 204-213 (2020) ISSN: 15304388, DOI: 10.1109/TDMR.2020.2974131
97. N. Mitrović, D. Danković, B. Randelović, Z. Prijić, **N. Stojadinović**, "Modeling of Static Negative Bias Temperature Stressing in p-channel VDMOSFETs using Least Square Method", *Informacije MIDE M, Journal of Microelectronics, Electronic Components and Materials*, vol. 50, no. 3, pp. 205-214 (2020) ISSN 0352-9045, doi.org/10.33180/InfMIDEM2020.305

PAPERS AT INTERNATIONAL CONFERENCES

1. **N.D. Stojadinović** and R.S. Popović, "A Study of Dislocations Induced in Emitter Phosphorus Diffusion during Silicon Planar Transistor Production: Generation, Elimination and Effects on Characteristics", *Semiconductor Silicon 1981*, edited by H.R. Huff, R.J. Kriegler and Y. Takeishi, Electrochem. Soc., Pennington, 1981 (pp. 844-855)
2. **N. Stojadinović**, E. Jelenković and S. Zdravković, "Influence of Emitter Diffusion Induced Dislocations on Reliability of Planar NPN Transistors", *Proc. 5th European Conference on Electrotechnics: Reliability in Electrical and Electronic Components and Systems (EUROCON'82)*, edited by E. Laguer and J. Moltoft, Nort-Holland Publishing Co., Amsterdam 1982 (pp. 270-273)
3. **N. Stojadinović**, "Failure Mechanisms of Integrated Circuits", *Proc. 6th International Conference on Reliability in Electronics (RELECTRONIC'85)*, Budapest 1985 (pp. 422-445) (**Invited Paper**)
4. Z. Živić, A. Živić and **N. Stojadinović**, "The Effects of Avalanche Hot-Carrier Injection in a New NMOST Structure", *Proc. 6th International Conference on Reliability in Electronics (RELECTRONIC'85)*, Budapest 1985 (pp. 458-465)
5. **N. Stojadinović**, "Failure Mechanisms of VLSI Integrated Circuits", *Proc. 1st Symposium on Diagnostics and Yield*, edited by A. Jakubowski, Warsaw 1986 (**Invited Paper**)
6. S. Golubović, S. Dimitrijević, D. Župac, M. Pejović and **N. Stojadinović**, "Gamma-Radiation Effects in CMOS Transistors", *Proc. 17th European Solid State Device Research Conference (ESSDERC'87)*, edited by G. Soncini, Bologna 1987 (pp. 725-728)
7. S. Mijalković and **N. Stojadinović**, "Multigrid Method: An Efficient Numerical Tool in VLSI Process Modeling", *Proc. 1st International Conference on Computer Technology, Systems and Applications (COMPEURO'87)*, edited by W.E. Proebster and H. Reiner, Hamburg 1987 (pp. 508-509)
8. S. Mijalković and **N. Stojadinović**, "Solution of the Diffusion Equation in VLSI Process Modeling by a Nonlinear Multigrid Algorithm", *Proc. 3rd International Conference on Numerical Methods and Approximation Theory (NMAT'87)*, edited by G.V. Milovanović, Niš, August 1987 (pp. 301-310)
9. D. Pantić, S. Mijalković, Z. Prijić and **N. Stojadinović**, "Optimization of CMOS Technology", *Proc. 6th Scientific-Technical Conference with International Participation (MICROELECTRONICS'88)*, Botevgrad 1988 (pp. 7-12) (**Invited Paper**)
10. S. Mijalković, D. Pantić and **N. Stojadinović**, "On Efficiency of Multigrid Methods in Two-Dimensional Impurity Redistribution Simulation", *Proc. 3rd International Conference on Simulation of Semiconductor Devices and Processes (SISDEP'88)*, edited by G. Baccarani and M. Rudan, Bologna September 26-28 1988 (pp. 463-474)

11. **N. Stojadinović** and S. Dimitrijević, "Instabilities in MOS Transistors", *Proc. 7th International Symposium on Reliability in Electronics (RELECTRONIC'88)*, Budapest 1988 (pp. 525-542) (**Invited Paper**) also *Microelectronics and Reliability* (1989)
12. Z. Prijić, S. Dimitrijević and **N. Stojadinović**, "Modeling of the Electrical Characteristics of CMOS Transistors at High Temperatures", *Proc. 17th Yugoslav Conference on Microelectronics (MIEL'89)*, edited by N. Stojadinović, Elsevier Advanced Technology, Oxford 1989 (pp. 325-330)
13. S. Golubović, M. Pejović, S. Dimitrijević and **N. Stojadinović**, "Effects of UV-Radiation Annealing on X-Ray Induced Damage in CMOS Transistors", *Proc. 17th Yugoslav Conference on Microelectronics (MIEL'89)*, edited by N. Stojadinović, Elsevier Advanced Technology, Oxford 1989 (pp. 833-838)
14. S. Dimitrijević and **N. Stojadinović**, "Yield Modeling in Integrated Circuit Production Control: A Critical Review", *Proc. 2nd Symposium on Diagnostics and Yield in Integrated Circuit Production*, edited by A. Jakubowski, Warsaw 1989 (pp. 16-23) (**Invited Paper**)
15. Z. Stamenković, S. Dimitrijević and **N. Stojadinović**, "Defect Size Distribution for Yield Modeling", *Proc. 2nd Symposium on Diagnostics and Yield in Integrated Circuit Production*, edited by A. Jakubowski, Warsaw 1989 (pp. 164-171)
16. **N. Stojadinović**, B. Pešić and D. Župac, "Failure Analysis of Integrated Circuits", *13th ISHM Conference*, Wrocław 1989 (**Invited Paper**)
17. Z. Stamenković and **N. Stojadinović**, "Test Structures for Integrated Circuit Yield Control", *Technical Proc. of SEMICON/Europa'91 - Defect Control and Related Yield Management*, Zurich 1991 (pp. 169-176)
18. S. Mijalković, D. Pantić, Z. Prijić, S. Mitrović and **N. Stojadinović**, "MUSIC - A Multigrid Simulator for IC Fabrication Processes", *Proc. of the 7th International Conference on the Numerical Analysis of Semiconductor Devices and Integrated Circuits (NASECODE VII)*, edited by J.J.H. Miller, Copper Mountain 1991 (pp. 111-113)
19. Z. Stamenković, S. Dimitrijević, **N. Stojadinović**, "Integrated Circuit Production Yield Assurance Based on Yield Analysis", *Proc. of the 8th International Symposium on Reliability in Electronics (RELECTRONIC'91)*, Budapest 1991
20. T. Brožek, B. Pešić, A. Jakubowski, **N. Stojadinović**, "The Influence of Ionizing Radiation on Dielectric Strength of the Gate Oxide", *8th International Symposium on Reliability in Electronics (RELECTRONIC'91)*, Budapest 1991
21. S. Mijalković, D. Pantić, Z. Prijić and **N. Stojadinović**, "Adaptive Multigrid Strategies for Simulation of Diffusion Processes", *Proc. 4th International Conference on Simulation of Semiconductor Devices and Processes (SISDEP'91)*, edited by W. Fichtner and D. Aemmer, Zürich, Switzerland 1991 (pp. 505-511)
22. Z. Pavlović, T. Jovanović, Z. Prijić, S. Ristić and **N. Stojadinović**, "An Improved Model for the Current-Voltage Characteristics of VDMOS Transistor in Strong Inversion", *Proc. of 1st International Seminar on Power Semiconductors (ISPS'92)*, Prague 1992 (pp. 94-101)
23. Z. Pavlović, Z. Prijić, S. Ristić and **N. Stojadinović**, "High Temperature Behavior of Power VDMOS Transistors", *Proc. of 3rd European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'92)*, October 1992, Schwäbisch Gmünd (pp. 47-50)
24. T. Brožek, B. Pešić, A. Jakubowski and **N. Stojadinović**, "Breakdown Characteristics of Gamma-Irradiated and Annealed Oxides", *Proc. of 3rd European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'92)*, October 1992, Schwäbisch Gmünd (pp. 391-394)
25. S. Mijalković, D. Pantić, Z. Prijić and **N. Stojadinović**, "Multigrid Approach for an Efficient Diffusion Simulation in VLSI Technology", *Proc. of the 15th Annual Semiconductor Conference (CAS'92)*, October 1992, Sinaia (pp. 29-38) (**Invited Paper**)

26. D. Pantić, S. Mijalković and **N. Stojadinović**, "The Efficient Simulation of Point Defects Diffusion by an Adaptive Multigrid Method", *22nd European Solid State Devices Research Conference (ESSDERC'92)*, Leuven 1992 (pp. 789-792), also *Microelectronic Engineering* (1992)
27. B. Pešić, T. Brozek, **N. Stojadinović** and A. Jakubowski, "Statistical Modeling of Multimodal Gate Oxide Breakdown Data Based on Mixed Weibull Distributions Concept", *Proc. 4th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'93)*, Bordeaux 1993 (pp. 171-176)
28. Z. Prijić, Z. Pavlović, S. Ristić, T. Jovanović and **N. Stojadinović**, "High Temperature Behaviour of MOS Devices - A Review", *Proc. of the 16th Annual Semiconductor Conference (CAS'93)*, Sinaia 1993 (pp. 425-434) (**Invited Paper**)
29. P. Habaš, D. Pantić, Z. Prijić and **N. Stojadinović**, "Technology CAD of Low-Voltage Power VDMOSFET", *Proc. 17th Annual Semiconductor Conference (CAS'94)*, Sinaia, October 1994 (pp. 501-510) (**Invited Paper**)
30. B. Pešić, D. Manić, Lj. Živković and **N. Stojadinović**, "Pre-Breakdown Electron Trapping in Irradiated and Annealed Oxides", *Proc. 20th International Conference on Microelectronics (MIEL'95)*, Niš, September 1995 (pp. 273-276)
31. N. Tošić, B. Pešić, and **N. Stojadinović**, "High Temperature Storage Life (HTSL) and High Temperature Reverse Bias (HTRB) Reliability Testing of Power VDMOSFETs", *Proc. 20th International Conference on Microelectronics (MIEL'95)*, Niš, September 1995 (pp. 285-288)
32. D. Pantić, S. Milenković, T. Trajković, V. Litovski and **N. Stojadinović**, "Inverse Modeling of Semiconductor Manufacturing Processes by Neural Networks", *Proc. 20th International Conference on Microelectronics (MIEL'95)*, Niš, September 1995 (pp. 321-326)
33. D. Pantić, T. Trajković, S. Milenković and **N. Stojadinović**, "Optimization of Power VDMOSFET's Process Parameters by Neural Networks", *Proc. 25th European Solid State Device Research Conference (ESSDERC'95)*, The Hague, September 1995 (pp. 793-796)
34. B. Pešić, N. Tošić, Z. Prijić, Z. Pavlović and **N. Stojadinović**, "Reliability of Power VDMOS Transistors", *Proc. 6th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'95)*, Bordeaux, October 1995 (pp. 111-116)
35. B. Pešić and **N. Stojadinović**, "Electron Trapping and Oxide Breakdown in Irradiated MOS Structures", *Proc. 14th International Conference on Reliability in Electronics (RELECTRONIC'95)*, Budapest, October 1995 (pp. 335-340)
36. B. Pešić and **N. Stojadinović**, "Breakdown Characteristics of Irradiated and Post-Irradiation Annealed Gate Oxides", *Proc. 9th International School on Condensed Matter Physics "Future Directions in Thin Film Science and Technology" (ISCMP'96)*, Varna, September 1996 (pp. 297-304) (**Invited Paper**)
37. Z. Prijić, D. Pantić and **N. Stojadinović**, "Educative Aspects of Power VDMOS Transistor Simulation", *Proc. of 3rd International Seminar on Power Semiconductors (ISPS'96)*, Prague, September 1996 (pp. 187-193)
38. N. Tošić, B. Pešić and **N. Stojadinović**, "Investigation of Failure Mechanisms in Power VDMOSFETs", *Proc. 6th International Symposium on the Physical & Failure Analysis of Integrated Circuits (IPFA'97)*, Singapore, July 1997 (pp. 191-195)
39. **N. Stojadinović**, S. Golubović, V. Davidović, S. Djorić-Veljković and S. Dimitrijević, "Modeling of Radiation-Induced Mobility Degradation in MOSFETs", *Proc. 21st International Conference on Microelectronics (MIEL'97)*, Niš, September 1997 (pp. 355-356)
40. N. Tošić, B. Pešić and **N. Stojadinović**, "Reliability Testing of Power VDMOS Transistors", *Proc. 21st International Conference on Microelectronics (MIEL'97)*, Niš, September 1997 (pp. 667-670)
41. T. Trajković, P. Igić and **N. Stojadinović**, "Extraction of Power VDMOS Transistor Model Parameters Using Neuralnetworks", *Proc. 21st International Conference on Microelectronics (MIEL'97)*, Niš, September 1997 (pp. 463-466)

42. N. Tošić, B. Pešić and **N. Stojadinović**, "High Temperature Reverse Bias Testing of Power VDMOS Transistors", *Proc. 8th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'97)*, Arcachon, October 1997 (pp. 1759-1762), also *Microelectronics Reliability* (1997)
43. Z. Pavlović, I. Manić, Z. Prijić and **N. Stojadinović**, "Temperature Dependence of ON-Resistance in High-Voltage Power VDMOS Transistors", *Proc. of 4th International Seminar on Power Semiconductors (ISPS'98)*, Prague, September 1998 (pp. 227-232)
44. Z. Pavlović, I. Manić, Z. Prijić and **N. Stojadinović**, "Influence of Channel Dopant Concentration and Temperature on Low-Voltage VDMOS Transistor ON-Resistance", *Proc. 21st International Semiconductor Conference (CAS'98)*, Sinaia, October 1998 (pp. 153-156)
45. P. Habaš and **N. Stojadinović**, "Mechanisms of Radiation-Induced Failures in Power Mosfets", *Proc. 6th International Conference on Mixed Design of Integrated Circuits And Systems (MIXDES'99)*, Krakow, June 1999 (pp. 43-54) (**Invited Paper**)
46. V. Davidović, S. Djorić-Veljković, S. Golubović and **N. Stojadinović**, "Room Temperature Relaxation of Irradiated and Cooled Power VDMOS Transistors", *Proc. 6th International Conference on Mixed Design of Integrated Circuits And Systems (MIXDES'99)*, Krakow, June 1999 (pp. 291-294)
47. V. Stojić, S. Vidanović, Z. Prijić, **N. Stojadinović**, "Object Oriented Approach to the Technology Processes Simulation of Devices and ICs Used in Telecom Applications", *Proc. 4th International Conference on Telecommunications in Modern Satellite, Cable and Broadcasting Services, (ITELSIKS 1999)* Niš, October 13-15 1999 (pp. 510-513)
48. S. Djorić-Veljković, S. Golubović, V. Davidović, and **N. Stojadinović**, "Power VDMOS Transistors Response to Lowered Temperature Conditions", *Proc. 22nd International Conference on Microelectronics (MIEL'00)*, Niš, May 2000 (pp. 383-386)
49. Z. Pavlović, I. Manić, Z. Prijić, V. Davidović, and **N. Stojadinović**, "Influence of Gate Oxide Charge Density on VDMOS Transistor ON-Resistance", *Proc. 22nd International Conference on Microelectronics (MIEL'00)*, Niš, May 2000 (pp. 663-666)
50. I. Manić, Z. Pavlović, Z. Prijić, V. Davidović, and **N. Stojadinović**, "Influence of γ -Irradiation on Electrical Characteristics of Power VDMOS Transistors", *Proc. 5th International Seminar on Power Semiconductors (ISPS'00)*, Prague, August 2000 (pp. 203-208)
51. S. Djorić-Veljković, V. Davidović, S. Golubović and **N. Stojadinović**, "Radiation Effects in Low-Temperature Stressed Power VDMOS Transistors", *Proc. 23rd International Semiconductor Conference (CAS'00)*, Sinaia, Romania, October 2000 (pp. 337-340)
52. I. Manić, Z. Pavlović, S. Golubović, S. Djorić-Veljković, V. Davidović, and **N. Stojadinović**, "Effects of γ -Irradiation on Drain Current and Transconductance in Power VDMOS Transistors", *Proc. 8th International Conference on Mixed Design of Integrated Circuits and Systems (MIXDES'01)*, Zakopane (Poland), June 2001 (pp. 333-338)
53. **N. Stojadinović**, S. Djorić-Veljković, I. Manić, V. Davidović, and S. Golubović, "Effects of Elevated-Temperature Bias Stressing on Radiation Response in Power VDMOS Transistors", *Proc. 8th International Symposium on the Physical & Failure Analysis of Integrated Circuits (IPFA'01)*, Singapore, July 2001 (pp. 243-248)
54. **N. Stojadinović**, S. Djorić-Veljković, V. Davidović, I. Manić, and S. Golubović, "Gamma-Irradiation Effects in Power MOSFETs for Applications in Communications Satellites", *Proc. 5th International Conference on Telecommunications in Modern Satellite, Cable and Broadcasting Services (TELSIKS'01)*, Niš (Yugoslavia), September 2001 (pp. 395-400)
55. **N. Stojadinović**, I. Manić, S. Djorić-Veljković, V. Davidović, S. Golubović, and S. Dimitrijević, "Mechanisms of Positive Gate Bias Stress Induced Instabilities in Power VDMOSFETs", *Proc. 12th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'01)*, Bordeaux (France), October 2001 (pp. 1373-1378), also *Microelectronics Reliability* (2001)

56. **N. Stojadinović**, I. Manić, S. Djorić-Veljković, V. Davidović, S. Golubović, and S. Dimitrijević, "Effects of Positive Gate Bias Stressing and Subsequent Recovery Treatment in Power VDMOSFETs", *Proc. 4th IEEE International Caracas Conference on Devices, Circuits, and Systems (ICDCS'02)*, Aruba (Dutch Caribbean), 15-17 April 2002, (pp. DO50-1 - DO50-8) **(Invited Paper)**
57. **N. Stojadinović**, I. Manić, S. Djorić-Veljković, V. Davidović, D. Danković, S. Golubović and S. Dimitrijević, "Spontaneous Recovery of Positive Gate Bias Stressed Power VDMOSFETs", *Proc. 23rd International Conference on Microelectronics (MIEL'02)*, Niš, May 2002 (pp. 717-722)
58. **N. Stojadinović**, S. Djorić-Veljković, I. Manić, V. Davidović and S. Golubović, "Effects of Positive Gate Bias Stress on Radiation Response in Power VDMOSFETs", *Proc. 23rd International Conference on Microelectronics (MIEL'02)*, Niš, May 2002 (pp. 723-726)
59. **N. Stojadinović**, S. Djorić-Veljković, I. Manić, V. Davidović and S. Golubović, "Radiation Response of Elevated-Temperature Bias Stressed Power VDMOSFETs" *Proc. 6th International Seminar on Power Semiconductors (ISPS'02)*, Prague, September 2002 (pp. 69-74)
60. **N. Stojadinović**, I. Manić, S. Djorić-Veljković, V. Davidović, D. Danković, S. Golubović, and S. Dimitrijević, "Mechanisms of Spontaneous Recovery in Positive Gate Bias Stressed Power VDMOSFETs", *Proc. 13th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'02)*, Rimini (Italy), October 2002 (pp.1465-1468), also *Microelectronics Reliability* (2002)
61. **N. Stojadinović**, I. Manić, S. Djorić-Veljković, V. Davidović and S. Golubović, "Electrical Stress Effects in Thick Gate Oxides for Power MOS Devices", *12th International School on Condensed Matter Physics (ISCMP'02)*, Varna, September 2002
62. I. Manić, S. Djorić-Veljković, V. Davidović, S. Golubović, S. Dimitrijević and **N. Stojadinović**, "Effects of Negative Gate Bias Stressing in Thick Gate Oxides for Power VDMOSFETs", *Proc. 12th Workshop on Dielectrics in Microelectronics (WODIM'02)*, Grenoble, November 2002 (pp. 41-44)
63. S. Djorić-Veljković, I. Manić, V. Davidović, S. Golubović and **N. Stojadinović**, "Effects of Burn-in Stressing on Post-Irradiation Annealing Response of Power VDMOSFETs", *Proc. 14th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'03)*, Bordeaux (France), October 2003 (pp.1455-1460), also *Microelectronics Reliability* (2003)
64. V. Davidović, I. Manić, S. Djorić-Veljković, D. Danković, S. Golubović, S. Dimitrijević, and **N. Stojadinović**, "Effects of Negative Gate Bias Stressing in Power VDMOSFETs", *Proc. 7th International Symposium on Microelectronics Technologies and Microsystems (MTM'03)*, Sozopol (Bulgaria), September 2003 (pp. 150-155)
65. Lj. Vračar, **N. Stojadinović**, B. Acković, et al., "Computer Controlled Equipment for Laboratory Exercises in Physics and Electronics", *Proc. International Conference on Computer as a Tool (IEE REGION 8 EUROCON'03)*, Ljubljana (Slovenija), September 2003 (pp.134-137)
66. **N. Stojadinović**, I. Manić, V. Davidović, D. Danković, S. Djorić-Veljković, S. Golubović, and S. Dimitrijević, "Effects of Electrical Stressing in Power VDMOSFETs", *Proc. IEEE Conference on Electron Devices and Solid-State Circuits (EDSSC'03)*, Hong Kong, December 2003 (pp. 291-296) **(Invited Paper)**
67. Z. Pavlović, I. Manić, and **N. Stojadinović**, "An Improved Analytical Model of IGBT in Forward Conduction Mode", *Proc. 24th International Conference on Microelectronics (MIEL'04)*, Niš, May 2004 (pp. 163-166)
68. M. Exarchos, D.N. Kouvatso, G.J. Papaioannou, V. Davidović, **N. Stojadinović**, L. Michalas, and A.T. Voutsas, "Characterization of Advanced Excimer Laser Crystallized Polysilicon Thin Film Transistors", *Proc. 24th International Conference on Microelectronics (MIEL'04)*, Niš, May 2004 (pp. 697-700)

69. S. Djorić-Veljković, I. Manić, V. Davidović, S. Golubović, and **N. Stojadinović**, "Burn-in Stressing Effects on Post-Irradiation Annealing Response of Power VDMOSFETs", *Proc. 24th International Conference on Microelectronics (MIEL '04)*, Niš, May 2004 (pp. 701-708)
70. **N. Stojadinović**, I. Manić, V. Davidović, D. Danković, S. Djorić-Veljković, S. Golubović, and S. Dimitrijević, "Electrical Stressing Effects in Power VDMOSFETs", *Proc. 7th International Seminar on Power Semiconductors (ISPS'04)*, Prague, September 2004 (pp. 109-114)
71. **N. Stojadinović**, "Effects of Electrical Stressing in Power VDMOSFETs", *Proc. 1st International Conference on Electrical and Electronic Engineering (ICEEE'04)*, Acapulco (Mexico), September 2004 (**Invited Paper**)
72. D.N. Kouvatso, V. Davidović, G.J. Papaioannou, **N. Stojadinović**, L. Michalas, M. Exarchos, A.T. Voutsas, and D.Goustouridis, "Effects of Hot Carrier and Irradiation Stresses on Advanced Excimer Laser Annealed Polycrystalline Silicon Thin Film Transistors", *Proc. 15th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'04)*, Zurich (Switzerland), October 2004, (pp. 1631-1636), also *Microelectronics Reliability* (2004)
73. **N. Stojadinović**, D. Danković, S. Djorić-Veljković, V. Davidović, I. Manić, and S. Golubović "Negative Bias Temperature Instability Mechanisms in p-Channel Power VDMOSFETs" *Proc. 16th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'05)*, Bordeaux (France), October 2005, (pp. 1343-1348), also *Microelectronics Reliability* (2005)
74. Lj.Vračar, **N. Stojadinović**, B. Pešić, "Computer as Powerful Tool in Reliability Testing of Thin Gate Dielectrics in MOS Devices", *Proc. International Conference on Computer as a Tool (IEE REGION 8 EUROCON'05)*, Ljubljana (Slovenija), September 2005 (pp. 1159-1162)
75. I. Manić, S. Djorić-Veljković, V. Davidović, D. Danković, S. Golubović, and **N. Stojadinović**, "Spontaneous Recovery in DC gate Bias Stressed Power VDMOSFETs", *Proc. 25th International Conference on Microelectronics (MIEL '06)*, Beograd, May 2006 (pp. 639-644)
76. D. Danković, I. Manić, S. Djorić-Veljković, V. Davidović, S. Golubović, and **N. Stojadinović**, "Lifetime Estimation in NBT Stressed p-Channel Power VDMOSFETs", *Proc. 25th International Conference on Microelectronics (MIEL '06)*, Beograd, May 2006 (pp. 605-608)
77. V. Davidović, **N. Stojadinović**, D. Danković, S. Golubović, I. Manić, S. Djorić-Veljković, and S. Dimitrijević, "Turn-around of Threshold Voltage in Gate Bias Stressed p-Channel Power VDMOS Transistors", *Proc. 8th International Seminar on Power Semiconductors (ISPS'06)*, Prague, September 2006 (pp. 85-89)
78. D. Danković, I. Manić, S. Djorić-Veljković, V. Davidović, S. Golubović, and **N. Stojadinović**, "NBT Stress-Induced Degradation and Lifetime Estimation in p-Channel Power VDMOSFETs", *Proc. 17th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'06)*, (Germany), October 2006 (pp. 1828-1833), also *Microelectronics Reliability* (2006)
79. **N. Stojadinović**, D. Danković, I. Manić, V. Davidović, S. Djorić-Veljković, and S. Golubović, "Impact of Negative Bias Temperature Instabilities on Lifetime in p-channel Power MOSFETs", *Proc. 8th International Conference on Telecommunications in Modern Satellite, Cable and Broadcasting Services (TELSIKS'07)*, Niš (Serbia), September 2007 (pp. 275-282) (**Invited Paper**)
80. D. Danković, I. Manić, V. Davidović, S. Djorić-Veljković, S. Golubović, **N. Stojadinović**, "Negative Bias Temperature Instabilities in Sequentially Stressed and Annealed in p-Channel Power VDMOSFETs", *Proc. 18th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF '07)*, Bordeaux (France), October 2007 (pp. 1400-1405), also *Microelectronics Reliability* (2007)
81. V. Davidović, DN. Kouvatso, **N. Stojadinović** and A.T. Voutsas, "Influence of Polysilicon Film Thickness on Radiation Response of Advanced Excimer Laser Annealed Polycrystalline Thin Film Transistors", *Proc. 18th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'07)*, Bordeaux (France), October 2007 (pp. 1841-1845), also *Microelectronics Reliability* (2007)

82. D. Danković, I. Manić, V. Davidović, S. Djorić-Veljković, S. Golubović, and **N. Stojadinović**, "New Approach in Estimating the Lifetime in NBT Stressed p-Channel Power VDMOSFETs", *Proc. 26th International Conference on Microelectronics (MIEL '08)*, Niš, May 2008 (pp. 599-602)
83. D. Danković, I. Manić, V. Davidović, S. Djorić-Veljković, S. Golubović, and **N. Stojadinović**, "Negative Bias Temperature Stress and Annealing Effects in p-Channel Power VDMOSFETs", *Proc. 9th International Seminar on Power Semiconductors (ISPS'08)*, Prague, August 2008 (pp. 127-132)
84. D. Danković, I. Manić, V. Davidović, S. Djorić-Veljković, S. Golubović, and **N. Stojadinović**, "Negative Bias Temperature Instability in n-Channel Power VDMOSFETs", *Proc. 19th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'08)*, Maastricht (Netherlands), September 2008 (pp. 1313-1317), also *Microelectronics Reliability* (2008)
85. E. Atanassova, **N. Stojadinović**, and A. Paskaleva, "Degradation Behaviour of T₂O₅ Stacks and its Dependence on the Gate Electrode", *Proc. 19th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'08)*, Maastricht (Netherlands), September 2008 (pp. 1193-1197), also *Microelectronics Reliability* (2008)
86. I. Manić, D. Danković, S. Djorić-Veljković, V. Davidović, S. Golubović, and **N. Stojadinović**, "Effects of Low Gate Bias Annealing in NBT Stressed p-Channel Power VDMOSFETs", *Proc. 20th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF'09)*, Arcachon, France, October 05-09 2009 (pp. 1003 - 1007), also *Microelectronics Reliability* (2009)
87. S. Djorić-Veljković, D. Danković, A. Prijić, I. Manić, V. Davidović, S. Golubović, Z. Prijić, and **N. Stojadinović**, "Degradation of p-channel Power VDMOSFETs under Pulsed NBT Stress", *Proc. 27th International Conference on Microelectronics (MIEL '10)*, Niš, May 2010 (pp. 443-446)
88. I. Manić, E. Atanassova, **N. Stojadinović**, and D. Spassov, "Effects of Constant Voltage Stress in Hf-doped Ta₂O₅ Stacks", *Proc. 27th International Conference on Microelectronics (MIEL '10)*, Niš, May 2010 (pp. 483-486)
89. I. Manić, D. Danković, S. Djorić-Veljković, A. Prijić, V. Davidović, S. Golubović, Z. Prijić, and **N. Stojadinović**, "Negative Bias Temperature Instability in p-Channel Power VDMOSFETs Under Pulsed Bias Stress", *Proc. 10th International Seminar on Power Semiconductors (ISPS 2010)*, Prague (Czech Republic) September 2010 (pp. 173-178)
90. **N. Stojadinović**, D. Danković, I. Manić, A. Prijić, V. Davidović, S. Djorić-Veljković, S. Golubović, Z. Prijić, "Threshold Voltage Instabilities in p-Channel Power VDMOSFETs Under Pulsed NBT Stress", *Proc. 21st European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF 2010)*, Gaeta (Italy) October 2010 (pp. 1278-1282), also *Microelectronics Reliability* (2010)
91. I. Manić, D. Danković, A. Prijić, V. Davidović, S. Djorić-Veljković, S. Golubović, and Z. Prijić, **N. Stojadinović**, "NBTI Related Degradation and Lifetime Estimation in p-Channel Power VDMOSFETs Under the Static and Pulsed NBT Stress Conditions", *Proc. 22nd European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF 2011)*, Bordeaux (France) 3-7 October 2011 (pp. 1540-1543), also *Microelectronics Reliability* (2011)
92. D. Danković, A. Prijić, I. Manić, Z. Prijić and **N. Stojadinović**, "Measurements of Negative Bias Temperature Instability (NBTI) in p-channel Power VDMOSFETs", *Proc. 11th International Seminar on Power Semiconductors (ISPS 2012)*, Prague (Czech Republic) August 2012 (pp. 240-245)
93. D. Danković, **N. Stojadinović**, Z. Prijić, I. Manić, and A. Prijić, "Recoverable and Permanent Components of V_T Shift in Pulsed NBT Stressed P-Channel Power VDMOSFETs", *Proc. 29th International Conference on Microelectronics (MIEL '14)*, Belgrade, May 2014 (pp. 297-300)
94. S. Djorić-Veljković, V. Davidović, D. Danković, I. Manić, S. Golubović, and **N. Stojadinović**, "Recovery Treatment Effects on Gamma Radiation Response in Electrically Stressed Power

- VDMOS Transistors", *Proc. 29th International Conference on Microelectronics (MIEL'14)*, Belgrade, May 2014 (pp. 293-296)
95. Z. Prijić, D. Danković, A. Prijić, I. Manić, **N. Stojadinović**, "A Method for Measuring NBTI Degradation in p-channel Power VDMOSFETs", *Proc. 50th International Conference on Microelectronics, Devices and Materials (MIDEM 2014)*, Ljubljana (Slovenia), October 2014 (pp. 9-16) (**Invited Paper**)
 96. M. Marjanović, D. Danković, V. Davidović, A. Prijić, **N. Stojadinović**, Z. Prijić, N. Janković, "Modeling and PSPICE simulation of radiation stress influence on threshold voltage shifts in p-channel power VDMOS transistors", *Proc. 3rd International Conference on Radiation and Applications in Various Fields of Research (RAD 2015)*, Budva (Montenegro) 8-12 June 2015 (pp. 405-408)
 97. V. Davidović, A. Paskaleva, D. Spassov, E. Guziewicz, T. Krajewski, S. Golubović, S. Đorić-Veljković, I. Manić, D. Danković, **N. Stojadinović**, "Electrical and Charge Trapping Properties of HfO₂/Al₂O₃ Multilayer Dielectric Stacks", *Proc. 30th International Conference on Microelectronics, (MIEL 2017)* Niš, October 2017 (pp. 143-146)
 98. D. Danković, I. Manić, V. Davidović, **N. Stojadinović**, Z. Prijić, S. Đorić-Veljković, A. Prijić, A. Paskaleva, D. Spassov, S. Golubović, "Modelling of Threshold Voltage Shift in Pulsed NBT Stressed p-Channel Power VDMOSFETs", *Proc. 30th International Conference on Microelectronics, (MIEL 2017)* Niš, October 2017 (pp. 147-150)
 99. **N. Stojadinović**, "NBTI and Radiation Related Degradation and Lifetime Estimation in Power VDMOSFETs", *Proc. IEEE Summer School Nanoelectronic technologies & devices: From basic principle to highly reliable application*, vol. 2, Toulouse, July 10-14, 2017 (pp. 71-92) (**Invited Lecture**)
 100. **N. Stojadinović**, S. Djorić-Veljković, V. Davidović, S. Golubović, S. Stankovic, A. Prijić, Z. Prijić, I. Manić, D. Danković, "NBTI and irradiation related degradation mechanisms in power VDMOS transistors", *29th European Symposium on the Reliability of Electron Devices, Failure Physics and Analysis (ESREF)*, Aalborg, Denmark, October 01-05, 2018 (pp. 135-141) DOI: 10.1016/j.microrel.2018.07.138 (**invited paper**)
 101. D. Danković, **N. Stojadinović**, "NBTI and radiation related degradation and lifetime estimation in power VDMOSFETs", *The 2018 International Symposium on Industrial Electronics – INDEL*, Banja Luka, Republic of Srpska, Bosnia and Herzegovina, 1-3 November 2018 (**invited paper**)
 102. D. Spassov, A. Paskaleva, V. Davidović, S. Djorić-Veljković, S. Stanković, **N. Stojadinović**, Tz. Ivanov, and T. Stanchev, "Impact of γ Radiation on Charge Trapping Properties of Nanolaminated HfO₂/Al₂O₃ ALD Stacks", *Proc. 31th International Conference on Microelectronics (MIEL'19)*, Niš, September 16-18, 2019 (pp. 59-62) DOI: 10.1109/MIEL.2019.8889600, ISBN: 978-172813419-2
 103. N. Mitrović, D. Danković, Z. Prijić, **N. Stojadinović**, "Modelling of δ vt in NBT stressed P-channel power VDMOSFETS", *Proc. 31th International Conference on Microelectronics (MIEL'19)*, Niš, September 16-18, 2019 (pp. 177-180) DOI: 10.1109/MIEL.2019.8889584, ISBN: 978-172813419-2

PAPERS IN NATIONAL JOURNALS

1. **N. Stojadinović**, S. Mijalković i D. Pantić, "Modeliranje procesa i komponenata integrisanih kola na Elektronskom fakultetu u Nišu", *Informacije MIDEM*, vol. 17, pp. 142-150 (1987)
2. **N. Stojadinović**, I. Manić, V. Davidović, D. Danković, S. Djorić-Veljković, S. Golubović, S. Dimitrijević, "Effects of Gate Bias Stressing in Power VDMOSFETs", *Serbian Journal of Electrical Engineering*, vol. 1, pp. 89-101 (2003) ISSN 1451-4869
3. D. Danković, I. Manić, V. Davidović, A. Prijić, S. Djorić-Veljković, S. Golubović, Z. Prijić, **N. Stojadinović**, "Lifetime Estimation in NBT-Stressed P-Channel Power VDMOSFETs", *Facta Universitatis: Series Automatic Control and Robotics*, vol. 11, no. 1, pp. 15-23 (2012) ISSN 1820-6417

4. M. Marjanović, D. Danković, V. Davidović, A. Prijić, **N. Stojadinović**, Z. Prijić, N. Janković, "Modeling and PSPICE simulation of radiation stress influence on threshold voltage shifts in p-channel power VDMOS transistors", *Radiation and Applications in Physics, Chemistry, Biology, Medical Sciences, Engineering and Environmental Sciences*, vol. 1, issue 1, pp. 26-30 (2016) DOI: 10.21175/RadJ.2016.01.05
5. I. Manić, D. Danković, V. Davidović, A. Prijić, S. Djorić-Veljковиć, S. Golubović, Z. Prijić, **N. Stojadinović**, "Effects of Pulsed Negative Bias Temperature Stressing in P-Channel Power VDMOSFETs", *Facta Universitatis, Series: Electronics and Energetics*, vol. 29, no. 3, pp. 49-60 (2016) (invited paper) ISSN: 0353-3670 (**Invited Paper**)
6. V. Davidović, D. Danković, S. Golubović, S. Djorić-Veljковиć, I. Manić, Z. Prijić, A. Prijić, **N. Stojadinović**, "NBT Stress and Radiation Related Degradation and Underlying Mechanisms in Power VDMOSFETs", *Facta Universitatis, Series: Electronics and Energetics*, vol. 31, no. 3, pp. 367-388 (2018) (**Invited Paper**) ISSN: 0353-3670
7. N. Mitrović, D. Danković, Z. Prijić, **N. Stojadinović**, "Modeling of NBTI degradation in p-channel VDMOSFETs", *Journal of Applied Engineering Science*, vol. 18, no. 4, pp. 515-519, DOI:10.5937/jaes0-26760

PAPERS AT NATIONAL CONFERENCES

1. **N. Stojadinović** i V. Cvekić, "Optimizacija tehnoloških parametara u varikap diodi sa superstrmim prelazom", *Zbornik radova III Jugoslovenskog simpozijuma o mikroelektronici, (MIEL '75)*, Niš 1975 (pp. T.81-T88)
2. **N. Stojadinović** i V. Cvekić, "Projektovanje raspodele koncentracije primesa u varikap diodi sa superstrmim prelazom", *Zbornik radova XIX Jugoslovenske konferencije za ETAN*, Ohrid 1975 (II sveska, pp. 1281-1288)
3. **N. Stojadinović** i V. Cvekić, "Jedan nov, tačniji analitički izraz za raspodelu koncentracije primesa u varikap diodi sa superstrmim prelazom", *Zbornik radova XI Jugoslovenskog simpozijuma o elektronskim sastavnim delovima i materijalima (SD '75)*, Ljubljana 1975 (pp. 105-111)
4. R. Popović i **N. Stojadinović**, "Eliminacija dislokacija na ivicama emitora planarnih NPN tranzistora depozicijom bornog stakla", *Zbornik radova XX Jugoslovenske konferencije za ETAN*, Opatija 1976 (II sveska, pp. 1335-1343)
5. R. Popović, B. Vidanović, Lj. Ristić i **N. Stojadinović**, "Zavisnost probojnog napona i dinamičkog otpora nisko-naponskih Zener-dioda od tehnologije formiranja P-N spoja", *Zbornik radova XX Jugoslovenske konferencije za ETAN*, Opatija 1977 (II sveska, pp. 1361-1369)
6. **N. Stojadinović**, Lj. Ristić i B. Vidanović, "Nova mogućnost za realizaciju nisko-naponskih Zener-dioda", *Zbornik radova XXI Jugoslovenske konferencije za ETAN*, Banja Luka 1977 (I sveska, pp. 285-292)
7. **N. Stojadinović**, B. Vidanović i Lj. Ristić, "Aproksimativni izraz za plitke profile fosfora u silicijumu", *Zbornik radova XIV Jugoslovenskog simpozijuma o elektronskim sastavnim delovima i materijalima (SD '87)*, Ljubljana 1978 (pp. 179-183)
8. **N. Stojadinović** i R. Popović, "Nov tehnološki postupak za eliminaciju dislokacija na ivicama emitora planarnih NPN tranzistora", *Zbornik radova XXIII Jugoslovenske konferencije za ETAN*, Maribor 1979 (I sveska, pp. 331-338)
9. **N. Stojadinović**, "Uslovi za formiranje dislokacija difuzijom fosfora u silicijumu", *Zbornik radova XVI Jugoslovenskog simpozijuma o elektronskim sastavnim delovima i materijalima (SD '80)*, Ljubljana 1980 (pp. 231-238)
10. **N.D. Stojadinović**, S.Ž. Mijalković i S.S. Dimitrijević, "Uticaj dislokacija izazvanih emitorskom difuzijom fosfora na inverznu struju N+-P spoja", *Zbornik radova IX Jugoslovenskog simpozijuma o mikroelektronici (MIEL '81)*, Ljubljana 1981 (pp. 15-23)

11. **N. Stojadinović**, E. Jelenković i S. Zdravković, "Uticaj dislokacija izazvanih emitorskom difuzijom fosfora na pouzdanost planarnih NPN tranzistora", *Zbornik radova XXV Jugoslovenske konferencije za ETAN*, Mostar 1981 (I sveska, pp. 425-432)
12. **N. Stojadinović** i S. Ristić, "Uzroci otkaza integrisanih kola", *Zbornik radova XVII Jugoslovenskog simpozijuma o elektronskim sastavnim delovima i materijalima (SD '81)*, Ljubljana 1981 (pp. 1-14) (**Rad po pozivu**)
13. **N. Stojadinović**, S. Mijalković i S. Dimitrijević, "Testne strukture za analizu pouzdanosti i uzroka otkaza u integrisanim kolima", *Zbornik radova XVII Jugoslovenskog simpozijuma o elektronskim sastavnim delovima i materijalima (SD '81)*, Ljubljana 1981 (pp. 15-28) (**Rad po pozivu**)
14. **N. Stojadinović**, "Projektovanje integrisanih kola: modeliranje procesa", *Zbornik radova X Jugoslovenskog simpozijuma o mikroelektronici (MIEL '82)*, Banja Luka 1982 (pp. 5-46) (**Rad po pozivu**)
15. **N. Stojadinović**, S. Mijalković i S. Dimitrijević, "Uticaj defekata pakovanja na inverznu struju P+-N spoja", *Zbornik radova X Jugoslovenskog simpozijuma o mikroelektronici (MIEL '82)*, Banja Luka 1982 (pp. 283-290)
16. Z. Pavlović i **N. Stojadinović**, "Uticaj bočnog dela emitorskog spoja na temperaturnu zavisnost strujnog pojačanja tranzistora snage", *Zbornik radova X Jugoslovenskog simpozijuma o mikroelektronici (MIEL '82)*, Banja Luka 1982 (pp. 277-282)
17. **N. Stojadinović**, S. Dimitrijević, S. Mijalković i E. Jelenković, "Pouzdanost P-kanalnih MOS tranzistora u CMOS integrisanim kolima", *Zbornik radova XXVI Jugoslovenske konferencije za ETAN*, Subotica 1982 (I sveska, pp. 467-474)
18. **N. Stojadinović**, Z. Pavlović i S. Milosavljević, "Uticaj bočnog dela emitorskog spoja na strujno pojačanje tranzistora snage", *Zbornik radova XVIII Jugoslovenskog simpozijuma o elektronskim sastavnim delovima i materijalima (SD '82)*, Ljubljana 1982 (pp. 45-54)
19. **N. Stojadinović**, S. Dimitrijević and Z. Živić, "Sudden Failures of CMOS Transistors", *Zbornik radova XI Jugoslovenskog simpozijuma o mikroelektronici (MIEL '83)*, Zagreb 1983 (pp. 419-426)
20. **N. Stojadinović**, S. Dimitrijević, S. Mijalković i Z. Živić, "Nestabilnosti napona praga N-kanalnih i P-kanalnih MOS tranzistora u CMOS integrisanim kolima", *Zbornik radova XXVII Jugoslovenske konferencije za ETAN*, Struga 1983 (V sveska, pp. 299-306)
21. Z. Pavlović, S. Milosavljević i **N. Stojadinović**, "Eksperimentalna analiza strujnog pojačanja tranzistora snage", *Zbornik radova XXVII Jugoslovenske konferencije za ETAN*, Struga 1983 (V sveska, pp. 243-249)
22. Z. Živić i **N. Stojadinović**, "Pouzdanost i mehanizmi otkaza CMOS integrisanih kola realizovanih VDIN procesom", *Zbornik radova XIX Jugoslovenskog simpozijuma o elektronskim sastavnim delovima i materijalima (SD '83)*, Ljubljana 1983 (pp. 101-109)
23. **N. Stojadinović**, S. Dimitrijević and S. Mijalković, "Threshold Voltage Instabilities of CMOS Transistors Induced by Gate Bias Stress", *Zbornik radova XII Jugoslovenskog simpozijuma o mikroelektronici (MIEL '84)*, Niš 1984 (pp. 94-103)
24. **N. Stojadinović**, D. Dimitrijević i S. Pešanović, "Uticaj ubrzanog temperaturnog testiranja radnog veka na niskofrekventni šum bipolarnih tranzistora", *Zbornik radova XII Jugoslovenskog simpozijuma o mikroelektronici (MIEL '84)*, Niš 1984 (pp. 105-111)
25. S. Milosavljević, D. Dimitrijević, D. Janković i **N. Stojadinović**, "Otkazi bipolarnih tranzistora snage usled termičkog zamora", *Zbornik radova XII Jugoslovenskog simpozijuma o mikroelektronici (MIEL '84)*, Niš 1984 (pp. 112-121)
26. Lj. Ristić, Lj. Nikolić, M. Gušić i **N. Stojadinović**, "Zavisnost probojnog napona dioda snage od tehnologije izrade P-N spoja", *Zbornik radova XII Jugoslovenskog simpozijuma o mikroelektronici (MIEL '84)*, Niš 1984 (pp. 263-270)

27. **N. Stojadinović** i S. Dimitrijević, "Efekti elektrostatičkog pražnjenja kod mikroelektronskih komponenata", *Zbornik radova I Srpskog simpozijuma iz primenjene elektrostatike*, Niš 1984 (pp. 24.1-24.10)
28. S. Dimitrijević and **N. Stojadinović**, "Instability Mechanisms of CMOS Integrated Circuits", *Zbornik radova XIII Jugoslovenskog simpozijuma o mikroelektronici (MIEL '85)*, Ljubljana 1985 (pp. 575-582)
29. **N. Stojadinović** i S. Dimitrijević, "Komponente MOS i CMOS integrisanih kola", *Zbornik radova VIII Jugoslovenskog seminara o primeni mikroprocesora (MIPRO '85)*, Rijeka 1985 (pp. 2.1-2.33) (**Rad po pozivu**)
30. S. Dimitrijević, D. Župac i. **N. Stojadinović**, "Metod za određivanje naelektrisanja kod MOS tranzistora", *Zbornik radova II Srpskog simpozijuma iz primenjene elektrostatike*, Niš 1986 (pp. 14.1-14.8)
31. S. Mijalković, Z. Nikolić, D. Pantić, D. Radivojević, A. Živić, **N. Stojadinović**, "Praktični aspekti modeliranja tehnologije integrisanih kola programom SUPREM II", *Zbornik radova XXII Jugoslovenskog simpozijuma o elektronskim sastavnim delovima i materijalima (SD'86)*, Otočec ob Krki 1986 (pp. 231-236)
32. S. Dimitrijević, D. Župac, **N. Stojadinović** and N. Janković, "Effects of High Gate Oxide Field Stressing on Silicon-Gate CMOS Transistors", *Zbornik radova XV Jugoslovenskog simpozijuma o mikroelektronici (MIEL '87)*, Banja Luka 1987 (pp. 445-454)
33. S. Dimitrijević, D. Župac and **N. Stojadinović**, "An Improvement of Commonly Used Expression for Drain Current of MOS Transistors", *Zbornik radova XV Jugoslovenskog simpozijuma o mikroelektronici (MIEL '87)*, Banja Luka 1987 (pp. 251-257)
34. D. Pantić, S. Mijalković, N. Janković i **N. Stojadinović**, "Praktični aspekti modeliranja CMOS integrisanih kola programom MINIMOS", *Zbornik radova XV Jugoslovenskog simpozijuma o mikroelektronici (MIEL '87)*, Banja Luka 1987 (pp.235-241)
35. **N. Stojadinović** i S. Dimitrijević, "Pouzdanost mikroelektronskih kola", *Zbornik radova sa Simpozijuma o obezbedjenju kvaliteta (CEOK '87)*, Ljubljana 1987 (pp.35-94) (**Rad po pozivu**)
36. S. Milošević i **N. Stojadinović**, "Novi način prikazivanja osobina bipolarnih tranzistora snage sa aspekta sekundarnog proboja", *Zbornik radova XXXII Jugoslovenske konferencije za ETAN*, Sarajevo 1988 (II sveska, pp. 99-105)
37. Z. Stamenković, S. Dimitrijević and **N. Stojadinović**, "Calculation of Chip Critical Area for Yield Modeling", *Zbornik radova XVIII Jugoslovenskog simpozijuma o mikroelektronici (MIEL '90)*, Ljubljana 1990 (pp. 133-136)
38. Z.D. Prijić, T.K. Jovanović, S.S. Dimitrijević and **N. D. Stojadinović**, "Analysis of Transconductance Temperature Dependence in CMOS Transistors", *Zbornik radova XVIII Jugoslovenskog simpozijuma o mikroelektronici (MIEL '90)*, Ljubljana 1990 (pp. 161-164)
39. S. Milošević i **N. Stojadinović**, "Uticaj zračenja na poluprovodničke komponente: PN spoj i odgovarajuće vrste dioda", *Zbornik radova XXXII Jugoslovenske konferencije za ETAN u pomorstvu*, Zadar 1990
40. S. Milošević i **N. Stojadinović**, "Uticaj zračenja na poluprovodničke komponente: bipolarni tranzistori", *Zbornik radova XXXII Jugoslovenske konferencije za ETAN u pomorstvu*, Zadar 1990
41. C.J. Patel, N.D. Janković, **N. Stojadinović** and J. Butcher, "Lateral Lambda Bipolar Transistors as a Highly Sensitive Radiation Dosimeter", *Proc. 19th Yugoslav Conference on Microelectronics (MIEL '91)*, Beograd 1991 (pp. 249-252)
42. S. Mijalković, D. Pantić, Z. Prijić, S. Mitrović and **N. Stojadinović**, "2-D IC Fabrication Processes Simulator Based on a Multigrid Method", *Proc. 19th Yugoslav Conference on Microelectronics (MIEL '91)*, Beograd 1991 (pp. 529-534)

43. S. Mijalković, D. Pantić, Z. Prijić, S. Mitrović and **N. Stojadinović**, "MUSIC - A Multigrid Simulator for IC Fabrication Processes: Application", *Proc. 19th Yugoslav Conference on Microelectronics (MIEL '91)*, Beograd 1991 (pp. 535-540)
44. Z. Stamenković and **N. Stojadinović**, "Comparison of Defects Size Distribution Functions for Integrated Circuit Yield Modeling", *Proc. 19th Yugoslav Conference on Microelectronics (MIEL '91)*, Beograd 1991 (pp. 541-546)
45. Z. Prijić, Z. Pavlović, S. Ristić i **N. Stojadinović**, "O postojanju tačke nultog temperaturnog koeficijenta kod VDMOS tranzistora snage", *Zbornik XXXVI Konferencije ETAN-a (ETAN '92)*, Kopaonik 1992 (pp. 77-85)
46. Z. Pavlović, Z. Prijić, S. Ristić i **N. Stojadinović**, "Raspodela temperature u oblasti kanala MOS tranzistora snage", *Zbornik radova XXXVI Konferencije ETAN-a (ETAN '92)*, Kopaonik 1992 (pp. 63-68)
47. S. Mitrović i **N. Stojadinović**, "Poredjenje jednomrežnih i višemrežnih tehnika za adaptivnu simulaciju procesa", *Zbornik radova I Srpske konferencije o mikro i optoelektronici (MIOPEL '92)*, Beograd 1992 (pp. 2.1.1-2.1.8)
48. S. Golubović, G. Ristić, S. Djorić i **N. Stojadinović**, "Efekti gama-zračenja kod VDMOS tranzistora snage", *Zbornik radova I Srpske konferencije o mikro i optoelektronici (MIOPEL '92)*, Beograd 1992, (pp. 1.2.3.)
49. D. Pantić, S. Mijalković and **N. Stojadinović**, "Efikasna simulacija procesa simultane difuzije tačkastih defekata i primesa adaptivnim multigrid metodom", *Zbornik radova XXXVII konferencije ETAN-a (ETAN '93)*, Beograd, Septembar 1993 (pp. 111-116)
50. S. Mitrović, S. Mijalković and **N. Stojadinović**, "Efikasna simulacija procesa difuzije u proluprovodnicima metodom geometrijskog razdvajanja", *Zbornik radova XXXVII konferencije ETAN-a (ETAN '93)*, Beograd, Septembar 1993 (pp. 117-122)
51. D. Pantić, S. Mijalković, S. Mitrović and **N. Stojadinović**, "The Efficient Simulation of Coupled Point Defect and Impurity Diffusion by an Adaptive Multigrid Method", *Proc. 2nd Serbian Conference on Microelectronics and Optoelectronics (MIOPEL '93)*, Niš, October 1993 (pp. 169-178)
52. **N. Stojadinović**, S. Djorić, S. Golubović and S. Dimitrijević, "Analysis of Gamma-Irradiation Induced Degradation Mechanisms in Power MOSFETs: Changes in Gate Oxide Charge and Interface Traps", *Proc. 2nd Serbian Conference on Microelectronics and Optoelectronics (MIOPEL '93)*, Niš, October 1993 (pp. 67-72)
53. S. Dimitrijević, S. Djorić, S. Golubović and **N. Stojadinović**, "Analysis of Gamma-Irradiation Induced Degradation Mechanisms in Power MOSFETs: Creation of Gate Oxide Charge and Interface Traps", *Proc. 2nd Serbian Conference on Microelectronics and Optoelectronics (MIOPEL '93)*, Niš, October 1993 (pp. 73-79)
54. T. Trajković, D. Pantić, Z. Prijić and **N. Stojadinović**, "Optimization of the Process Parameters for Power VDMOS Transistors' Technology", *Proc. 2nd Serbian Conference on Microelectronics and Optoelectronics (MIOPEL '93)*, Niš, October 1993 (pp. 197-202)
55. S. Mitrović, S. Mijalković and **N. Stojadinović**, "A Method for Diffusion Simulation in Nonplanar Geometries Convenient for Implementation on Parallel Computers", *Proc. 2nd Serbian Conference on Microelectronics and Optoelectronics (MIOPEL '93)*, Niš, October 1993 (pp. 191-195)
56. Z. Pavlović, T. Jovanović, Z. Prijić, S. Ristić and **N. Stojadinović**, "Temperature Dependence of On-Resistance in Power VDMOS Transistors", *Proc. 2nd Serbian Conference on Microelectronics and Optoelectronics (MIOPEL '93)*, Niš, October 1993 (pp. 87-92)
57. S. Djorić-Veljković, S. Golubović, V. Davidović i **N. Stojadinović**, "Uticaj različitih naprezanja na formiranje latentnih defekata tokom spontanog oporavka VDMOS tranzistora snage", *Zbornik radova XLIII jugoslovenske konferencije za ETRAN*, Zlatibor, 20.-22. septembar 1999, (sveska IV str. 139-141)

58. Z. Pavlović, M. Odalović, T. Premović, I. Manić, Z. Prijić, **N. Stojadinović**, "Uticaj gustine naelektrisanja u oksidu kanala na transkonduktansu VDMOS tranzistora snage", *Zbornik radova XLIII jugoslovenske konferencije za ETRAN*, Zlatibor, 20.-22. septembar 1999, (sveska IV str. 142-145)
59. S. Djorić-Veljković, S. Golubović, V. Davidović and **N. Stojadinović**, "Efekti niskih temperatura kod VDMOS tranzistora snage", *Zbornik radova XLIV jugoslovenske konferencije za ETRAN*, Soko Banja, 26.-29. jun 2000, (sveska IV str. 185-188)
60. S. Djorić-Veljković, **N. Stojadinović**, I. Manić, V. Davidović, S. Golubović, "Uticaj temperaturno-naponskih testova pouzdanosti na efekte zračenja kod VDMOS tranzistora snage", *Zbornik radova XLV jugoslovenske konferencije za ETRAN*, Bukovička Banja, 04.-07. jun 2001, (sveska IV str. 200-203)
61. **N. Stojadinović**, I. Manić, S. Golubović, V. Davidović, S. Djorić-Veljković, S. Dimitrijević, "Efekti naprezanja pozitivnom polarizacijom na gejtu kod VDMOS tranzistora snage" *Zbornik radova XLV jugoslovenske konferencije za ETRAN*, Bukovička Banja, 4.-7. jun 2001, (sveska IV str. 204-207)
62. **N. Stojadinović**, S. Djorić-Veljković, I. Manić, V. Davidović, S. Golubović, "Uticaj električnog naprezanja na otpornost VDMOS tranzistora snage na zračenje", *Zbornik radova XLVI jugoslovenske konferencije za ETRAN*, Banja Vrućica (Republika Srpska), 3-6 jun 2002, (sveska IV str. 142-144)
63. V. Davidović, S. Golubović, I. Manić, D. Danković, **N. Stojadinović**, S. Djorić-Veljković, S. Dimitrijević, "Primena tehnika za razdvajanje efekata naelektrisanja u oksidu i površinskih stanja kod VDMOS tranzistora snage", *Zbornik radova XLVI jugoslovenske konferencije za ETRAN*, Banja Vrućica (Republika Srpska), 3-6 jun 2002, (sveska IV str. 145-148)
64. I. Manić, V. Davidović, D. Danković, S. Golubović, **N. Stojadinović**, S. Djorić-Veljković, S. Dimitrijević, "Efekti naprezanja negativnom polarizacijom na gejtu kod VDMOS tranzistora snage", *Zbornik radova XLVII jugoslovenske konferencije za ETRAN*, Herceg Novi, 8-13 jun 2003, (sveska IV str. 183-186)
65. S. Djorić-Veljković, **N. Stojadinović**, I. Manić, V. Davidović, S. Golubović, "Uticaj temperaturno-naponskih testova pouzdanosti na efekte odžarivanja kod ozračenih VDMOS tranzistora snage", *Zbornik radova XLVII jugoslovenske konferencije za ETRAN*, Herceg Novi, 8-13 jun 2003, (sveska IV str. 187-190)
66. V. Davidović, **N. Stojadinović**, "Efekti naponskog naprezanja i jonizujućeg zračenja kod TFT MOS tranzistora", *Zbornik radova XLVIII jugoslovenske konferencije za ETRAN*, Čačak, 6-10 jun 2004 (sveska IV str. 121-124)
67. V. Davidović, **N. Stojadinović**, D. Danković, S. Golubović, I. Manić, S. Djorić-Veljković, S. Dimitrijević, "Turn-around efekat napona praga kod PMOS tranzistora napreznih pozitivnim naponima na gejtu", *Zbornik radova XLIX konferencije za ETRAN*, Budva, 05-10 jun 2005, (sveska IV str. 125-128)
68. D. Danković, I. Manić, V. Davidović, S. Golubović, N. Stojadinović, S. Djorić-Veljković, "Nestabilnosti P-kanalnog VDMOS tranzistora snage usled naponsko-temperaturnih naprezanja sa negativnom polarizacijom gejta", *Zbornik radova XLIX konferencije za ETRAN*, Budva, 05-10 jun 2005, (sveska IV str. 129-132) (nagrađen rad)
69. I. Manić, D. Danković, **N. Stojadinović**, "NBT Nestabilnosti kod P- i N-kanalnog VDMOS tranzistora snage", *Zbornik radova LII konferencije za ETRAN*, Palić, 08-12 jun 2008, (str. MO1.1-1-4)
70. D. Danković, I. Manić, V. Davidović, S. Golubović, **N. Stojadinović**, S. Djorić-Veljković, "Life Time Evaluation in p-channel Power VDMOSFETs Under NBT Stress", *Zbornik radova LII konferencije za ETRAN*, Palić, 08-12 jun 2008, (str. MO1.2-1-4) (nagrađen rad)
71. D. Danković, I. Manić, V. Davidović, S. Golubović, **N. Stojadinović**, S. Djorić-Veljković, "Instabilities in p-channel power VDMOSFETs Subjected to Multiple Negative Bias Temperature Stressing and Annealing", *Zbornik radova LIII konferencije za ETRAN*, Vrnjačka Banja, 15-18 jun 2009, (str. MO1.1-1-4)

72. Dj. Kostadinović, D. Danković, I. Manić, V. Davidović, S. Golubović, **N. Stojadinović**, S. Djorić-Veljković, "Efekti spontanog oporavka kod p-kanalnih VDMOS tranzistora snage napreznanih jakim električnim poljem u oksidu gejta", *Zbornik radova LIII konferencije za ETRAN*, Vrnjačka Banja, 15-18 jun 2009, (str. MO1.2-1-4)
73. D. Danković, A. Prijić, I. Manić, V. Davidović, S. Golubović, **N. Stojadinović**, Z. Prijić, S. Djorić-Veljković, "Instabilities in p-Channel Power VDMOSFETs Subjected to Pulsed Negative Bias Temperature Stressing", *Zbornik radova LIV konferencije za ETRAN*, Donji Milanovac, 7-10. jun 2010, (str. MO1.1-1-4)
74. I. Manić, **N. Stojadinović**, E. Atanassova, D. Spassov, "Constant Voltage Stressing of Hf-Doped Ta₂O₅ Stacks", *Zbornik radova LIV konferencije za ETRAN*, Donji Milanovac, 7-10. jun 2010, (str. MO1.2-1-4)
75. D. Danković, A. Prijić, I. Manić, V. Davidović, S. Golubović, Z. Prijić, **N. Stojadinović**, S. Đorić-Veljković "Određivanje perioda pouzdanog rada p-kanalnih VDMOS tranzistora snage podvrgnutih kontinualnim i impulsnim NBT napreznjima", *Zbornik radova LVI konferencije za ETRAN*, Zlatibor, 11-14 Jun 2012, (str. MO1.1-1-4)
76. I. Manić, D. Danković, **N. Stojadinović**, "Modelovanje napona praga p-kanalnih VDMOS tranzistora snage tokom naponsko temperaturnih napreznja i odžarivanja", *Zbornik radova LVI konferencije za ETRAN*, Zlatibor, 11-14 Jun 2012, (str. MO1.2-1-4)
77. D. Danković, A. Prijić, I. Manić, Z. Prijić, **N. Stojadinović**, "Naponsko temperaturna napreznja p-kanalnih VDMOS tranzistora snage", *Zbornik radova LVII konferencije za ETRAN*, Zlatibor, 3-6. jun 2013, (str. MO1.1-1-5)
78. S. Djorić-Veljković, I. Manić, V. Davidović, D. Danković, S. Golubović, **N. Stojadinović**, "Uticaj odžarivanja na oporavak električno napreznanih VDMOS tranzistora snage", *Zbornik radova LVII konferencije za ETRAN*, Zlatibor, 3-6. jun 2013, (str. MO1.2-1-6) (nagrađen rad)
79. A. Ilić, Z. Prijić, A. Prijić, V. Davidović, D. Danković, **N. Stojadinović**, "Mobilna eksperimentalna postavka za određivanje napona praga VDMOS tranzistora snage", *Zbornik radova LVIII konferencije za ETRAN*, Vrnjačka Banja, 2-5 Jun 2014, (str. MO1.2.1-4)
80. V. Davidović, A. Paskaleva, D. Spassov, E. Guziewicz, T. Krajewski, S. Đorić-Veljković, S. Golubović, I. Manić, D. Danković, **N. Stojadinović**, "Ispitivanje višeslojnih HfO₂/Al₂O₃ višeslojnih struktura za memorijske komponente", *Zbornik radova LXI konferencije za ETRAN*, Kladovo, 5-8 Jun 2017 (MO1.1.1- MO1.1.4) ISBN 978-86-7466-692-0
81. V. Davidović, D. Danković, S. Golubović, S. Đorić-Veljković, I. Manić, Z. Prijić, A. Prijić, **N. Stojadinović**, "Elektrohemijski procesi kod p-kanalnih VDMOS tranzistora snage pri sukcesivnom NBT napreznju i ozračivanju", *Zbornik radova LXII konferencije za ETRAN*, Palić, 11-14 Jun 2018 (MO1.1.1- MO1.1.4) ISBN 978-86-7466-752-1
82. Snežana Đorić-Veljković, Vojkan Davidović, Danijel Danković, Snežana Golubović and **Ninoslav Stojadinović**, "Procedure merenja električnih karakteristika napreznanih p-kanalnih VDMOS tranzistora snage", *Zbornik radova LXIII konferencije za ETRAN*, Srebrno jezero, 03-06 jun 2019, str. 601-604. ISBN 978-86-7466-785-9
83. Nikola Mitrović, Danijel Danković, Zoran Prijić, **Ninoslav Stojadinović**, "Modelovanje promenana napona praga p-kanalnih VDMOS tranzistora snage tokom NBT napreznja", *Zbornik radova LXIV konferencije za ETRAN*, Niš, 28-29 septembar 2020, str. 490-494. ISBN 978-86-7466-852-8